

Notice of References Cited

Application/Control No.

10/591,456

Applicant(s)/Patent Under
Reexamination
OGURA ET AL.

Examiner

JESSE A. ELBIN

Art Unit

2614

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-4,142,073	02-1979	Agneus et al.	381/174
*	B	US-2002/0181725	12-2002	Johannsen et al.	381/174
	C	US-			
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	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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	V	E.C.Ross et al., Effects of Silicon Nitride Growth Temperature on Charge Storage in the MNOS Structure, 1969, Applied Physics Letters, Volume 15 Number 12, 408-409.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.